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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/706,948	11/14/2003	James N. Pan	50432-655 7419			
7590 11/14/2005 McDERMOTT, WILL & EMERY			EXAMINER			
			PERALTA, GINETTE			
600 13th Street, Washington, D	N.W. C 20005-3096		ART UNIT	PAPER NUMBER		
•			2814			
			DATE MAILED: 11/14/2005	DATE MAILED: 11/14/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

	· · · · · · · · · · · · · · · · · · ·	Applica	tion No.	Applicant(s)	
Office Action Summary		10/706,	948	PAN ET AL.	
		Examin	er	Art Unit	
		Ginette	Peralta	2814	
Period fo	The MAILING DATE of this commun or Reply	ication appears on t	he cover sheet with the	correspondence addres	;s
WHIC - Exter after - If NO - Failui Any r	ORTENED STATUTORY PERIOD F CHEVER IS LONGER, FROM THE M resions of time may be available under the provisions SIX (6) MONTHS from the mailing date of this comm period for reply is specified above, the maximum streeto reply within the set or extended period for reply eply received by the Office later than three months a department term adjustment. See 37 CFR 1.704(b).	AILING DATE OF 7 of 37 CFR 1.136(a). In no a nunication. atutory period will apply and will, by statute, cause the a	THIS COMMUNICATION Event, however, may a reply be to will expire SIX (6) MONTHS from pplication to become ABANDON	DN. timely filed m the mailing date of this commu IED (35 U.S.C. § 133).	
Status					
2a) ☐ 3) ☐	Responsive to communication(s) file This action is FINAL. Since this application is in condition closed in accordance with the practi	2b)⊠ This action is for allowance exce _l	ot for formal matters, p		erits is
Dispositi	on of Claims		•		
5)□ 6)⊠ 7)⊠	Claim(s) <u>1-21</u> is/are pending in the a 4a) Of the above claim(s) <u>1-13</u> is/are Claim(s) is/are allowed. Claim(s) <u>14 and 15</u> is/are rejected. Claim(s) <u>16-21</u> is/are objected to. Claim(s) are subject to restrict	withdrawn from co			
Applicati	on Papers				,
10)	The specification is objected to by the The drawing(s) filed on is/are: Applicant may not request that any objected to Replacement drawing sheet(s) including The oath or declaration is objected to	a) accepted or lection to the drawing(s the correction is requ) be held in abeyance. So lired if the drawing(s) is o	ee 37 CFR 1.85(a). bjected to. See 37 CFR 1	• •
Priority u	inder 35 U.S.C. § 119				
12)	Acknowledgment is made of a claim All b) Some * c) None of: 1. Certified copies of the priority 2. Certified copies of the priority 3. Copies of the certified copies application from the Internation see the attached detailed Office action	documents have be documents have be of the priority docur nal Bureau (PCT R	een received. een received in Applica nents have been receivule 17.2(a)).	ntion No ved in this National Staç	ge
2) 🔲 Notici 3) 🔯 Inforn	e of References Cited (PTO-892) of Oraftsperson's Patent Drawing Review (Potation Disclosure Statement(s) (PTO-1449 or No(s)/Mail Date 3/14/05.		4) Interview Summar Paper No(s)/Mail [5) Notice of Informal 6) Other:		2)

DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of claims 14-21 in the reply filed on 7/28/05 is acknowledged.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35
 U.S.C. 102 that form the basis for the rejections under this section made in this
 Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 3. Claims 14 and 15 are rejected under 35 U.S.C. 102(e) as being anticipated by Kim et al. (US Pat. Pub. 2004/0063286 A1).

Regarding claim 14, Kim et al. discloses in Figs.3A to 3R a method of forming a multiple-channel semiconductor device that comprises the steps of forming a stack on the substrate, the stack including at least two lightly doped channel regions 16 vertically separated from each other and from the substrate by insulator layers 14, and a gate electrode 48 separated from the channel regions 16 by an insulator layer 14; forming an oxide liner 46 (shown in Fig. 3O-3R) on sidewalls of the gate electrode 48; forming source and drain regions 32 contacting

sidewalls of the channel regions; and forming gate electrode spacers 40 on the oxide liner 46 on the gate electrode 48.

Regarding claim 15, Kim et al. discloses that the step of forming an oxide liner includes forming a thermal oxide liner 46 on the sidewalls of the gate electrode 48, as shown in Fig. 3O.

Allowable Subject Matter

4. Claims 16-21 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The primary reason for the allowance of the claims is the inclusion of the feature of forming gate electrode spacers on the oxide liner by depositing nitride on the oxide liner and the gate electrode and performing a spacer etch stopping on the insulator layer separating the gate electrode from the channel regions in combination with forming a multiple channel semiconductor device by the steps of forming a stack on a substrate that includes at least two lightly doped channel regions and a gate electrode, forming an oxide liner on the sidewalls of the gate electrode; and forming source and drain regions contacting sidewalls of the channel regions which is not anticipated nor rendered obvious over the prior art of record. The prior art of record includes Kim et al. as discussed above and Krivokapic (U. S. Pat. 6,919,250 B2), where Krivokapic discloses a method of forming a semiconductor device that includes forming a stack of alternating

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semiconductor and insulating material, forming an oxide liner on sidewalls of the gate electrode; and forming source and drain regions contacting sidewalls of the semiconductor regions, but does not include forming multiple channels or forming gate electrode spacers on the oxide liner that stop on the insulator layer separating the gate electrode from the channel regions as disclosed in claim 16, and subsequent claims that depend from claim 16.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ginette Peralta whose telephone number is (571) 272-1713. The examiner can normally be reached on Monday to Friday 8:00 AM- 5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

GP

HOAL PHAM EXAMINER